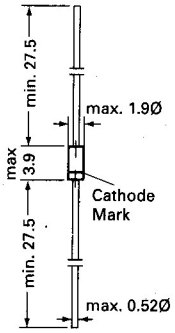
BA243A, BA244A

Silicon Epitaxial Planar Diode Switches
for electronic band-switching in radio and TV tuners in the frequency range of 50 ... 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped.
Details see "Taping".



Glass case JEDEC DO-35
54 A 2 according to DIN 41 880

Weight approx. 0.13 g
Dimensions in mm

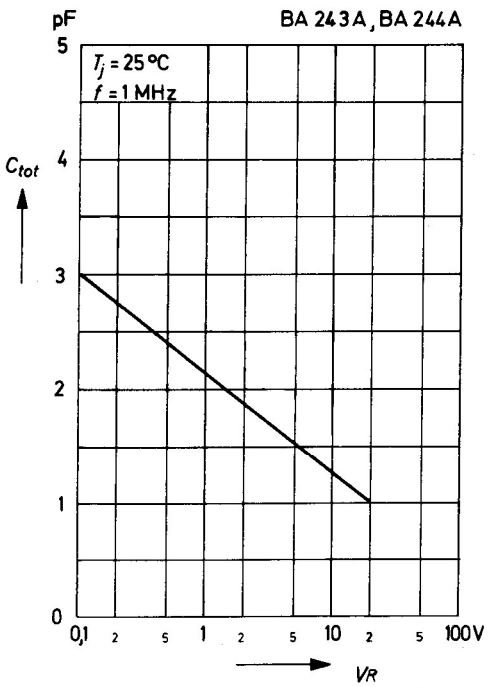
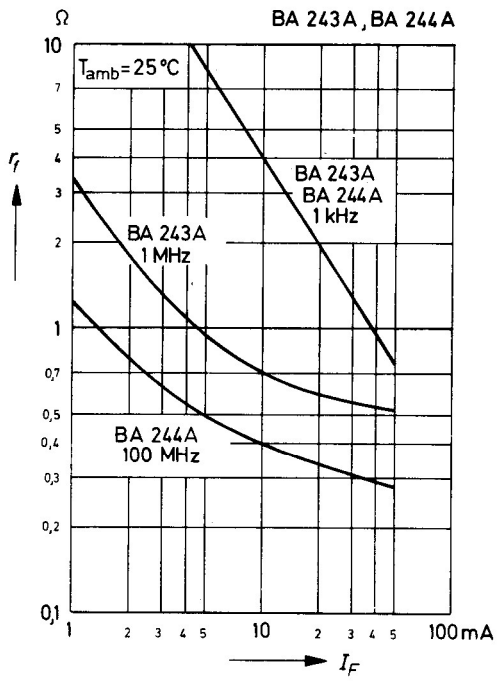
Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current at T_{amb} = 25 °C	I_F	100	mA
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to + 150	°C

Characteristics at T_{amb} =25 °C

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	-	-	1	V
Leakage Current at V_R = 20 V at V_R = 15 V, T_{amb} = 60 °C	 I_R I_R	 - -	 - -	 50 1	 nA µA
Dynamic Forward Resistance at f = 50 to 1000 MHz, I_F = 10 mA **BA243A** **BA244A**	 r_f r_f	 - -	 0.7 0.4	 1 0.5	 Ω Ω
Relative Variation of Dynamic Forward Resistance with the Variation of Forward Current in the Range of I_F = 2 to 40 mA	$\frac{\Delta r_f \cdot 100}{r_f \cdot \Delta I_F}$	-	5	-	%/mA
Capacitance at V_R = 3 V, f = 1 MHz	C_{tot}	-	-	1.8	pF
Relative Variation of Capacitance with the Variation of Reverse Voltage in the Range of V_R = 7 to 20 V, f = 100 MHz	$\frac{\Delta C_{tot} \cdot 100}{C_{tot} \cdot \Delta V_R}$	-	1	-	%/V
Series Inductance across Case	L_s	-	2.5	-	nH

Capacitance versus reverse voltage



Dynamic forward resistance versus forward current